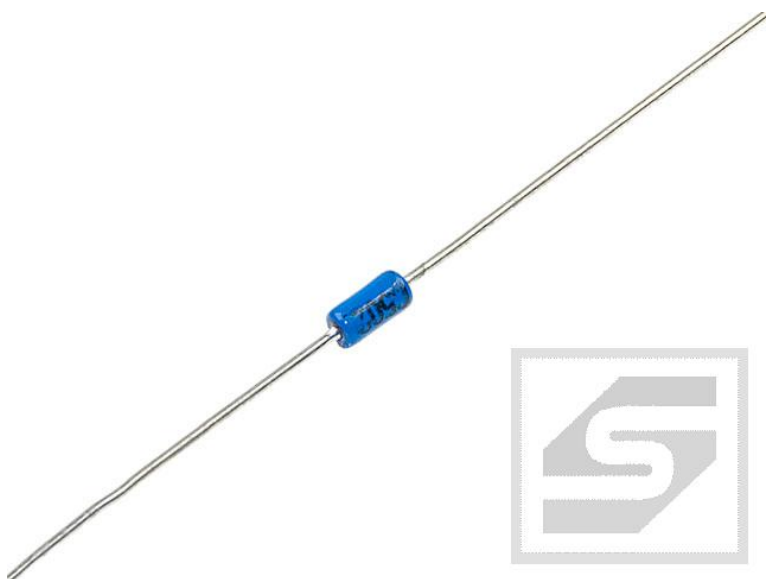




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Diak DB4 SGS



Dane techniczne:

Nazwa: Diak DB4 SGS

Napięcie przełączania: 40V

Prąd przewodzenia: 2A

Obudowa: DO35

Montaż: THT

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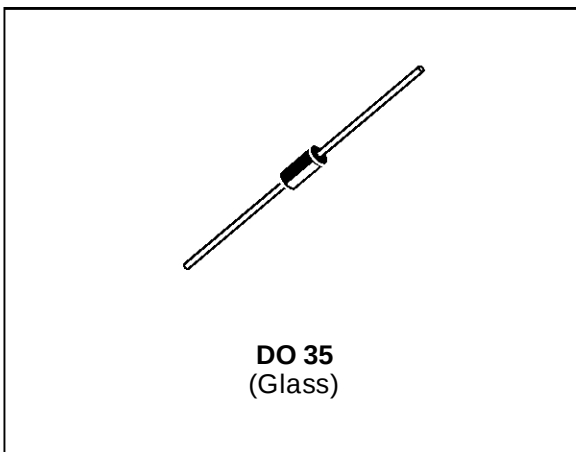
Robert Stępień Hurtownia Części Elektronicznych; Adres: ul. Wolumen 2, pawilon 71; 01-912 Warszawa; tel.: 601 296 402 /
sklep@podzespoly-elektroniczne.pl

TRIGGER DIODES
FEATURES

- V_{BO} : 32V / 34V / 40V VERSIONS
- LOW BREAKOVER CURRENT

DESCRIPTION

High reliability glass passivation insuring parameter stability and protection against junction contamination.


ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
P	Power dissipation on printed circuit (L = 10 mm)	$T_a = 65\text{ }^{\circ}\text{C}$	150	mW
I_{TRM}	Repetitive peak on-state current	$t_p = 20\text{ }\mu\text{s}$ $F = 100\text{ Hz}$	2	A
T_{stg} T_j	Storage and operating junction temperature range		- 40 to + 125 - 40 to + 125	$^{\circ}\text{C}$ $^{\circ}\text{C}$

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-a)}$	Junction to ambient	400	$^{\circ}\text{C/W}$
$R_{th(j-l)}$	Junction-leads	150	$^{\circ}\text{C/W}$

DB3 / DB4 / DC34

ELECTRICAL CHARACTERISTICS (T_j = 25°C)

Symbol	Parameter	Test Conditions		Value			Unit
				DB3	DC34	DB4	
V _{BO}	Breakover voltage *	C = 22nF ** see diagram 1	MIN	28	30	35	V
			TYP	32	34	40	
			MAX	36	38	45	
[I+V _{BO} -I-V _{BO}]	Breakover voltage symmetry	C = 22nF ** see diagram 1	MAX	± 3			V
IΔV± I	Dynamic breakover voltage *	ΔI = [I _{BO} to I _F =10mA] see diagram 1	MIN	5			V
V _O	Output voltage *	see diagram 2	MIN	5			V
I _{BO}	Breakover current *	C = 22nF **	MAX	100	50	100	μA
t _r	Rise time *	see diagram 3	TYP	1.5			μs
I _B	Leakage current *	V _B = 0.5 V _{BO} max see diagram 1	MAX	10			μA

* Electrical characteristic applicable in both forward and reverse directions.

** Connected in parallel with the devices.

DIAGRAM 1 : Current-voltage characteristics

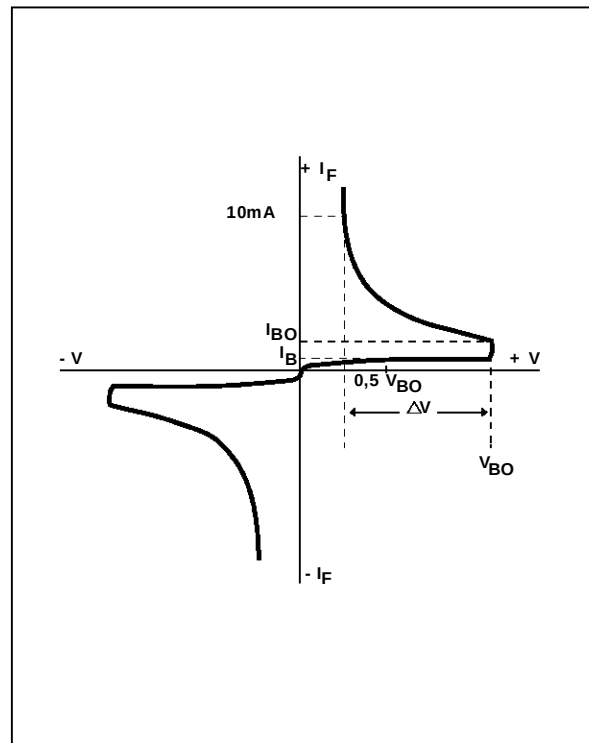
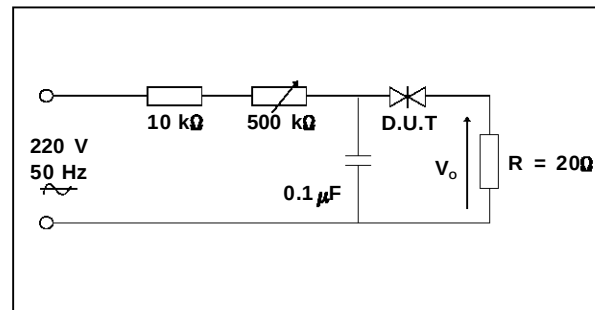


DIAGRAM 2 : Test circuit for output voltage



**DIAGRAM 3 : Test circuit see diagram 2.
Adjust R for I_p=0.5A**

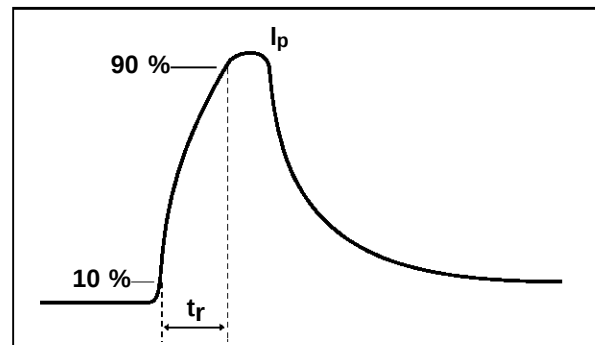


Fig.1 : Power dissipation versus ambient temperature (maximum values)

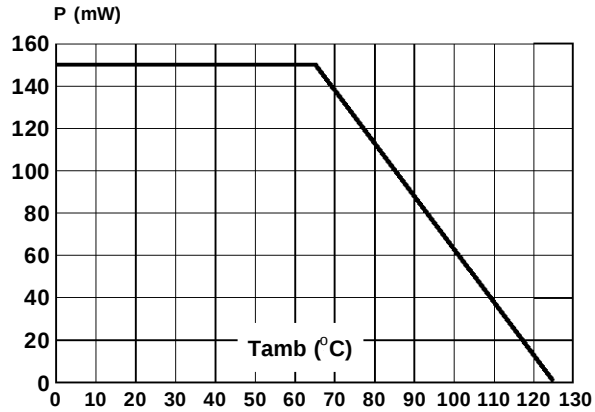


Fig.2 : Relative variation of V_{BO} versus junction temperature (typical values)

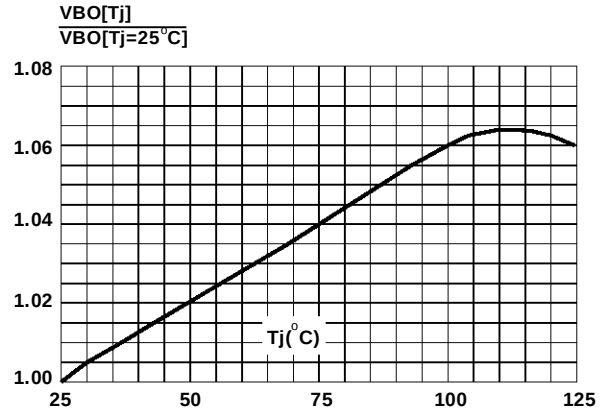
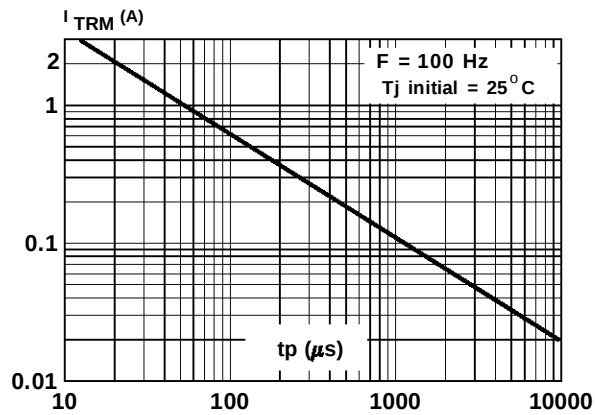
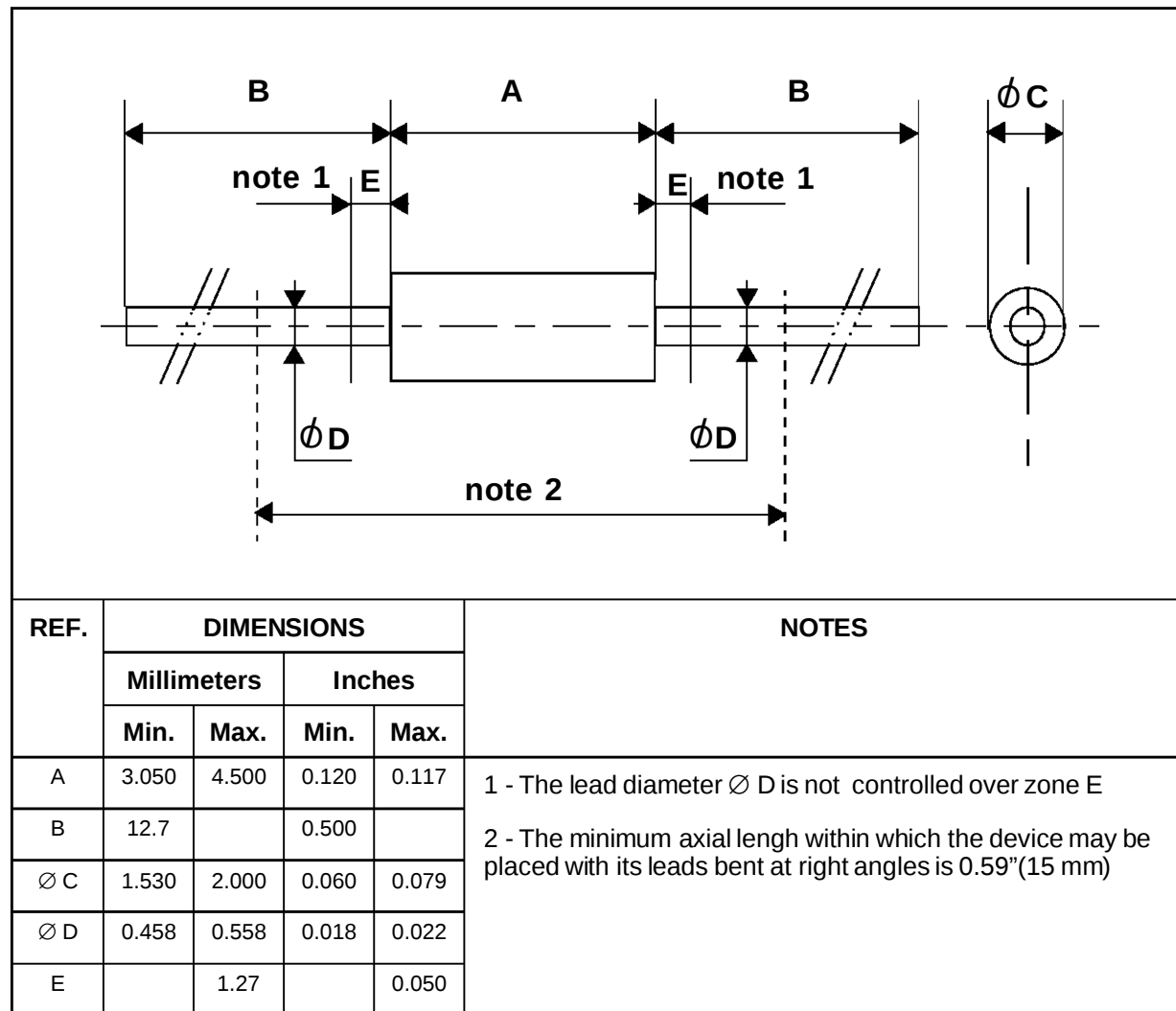


Fig.3 : Peak pulse current versus pulse duration (maximum values)



DB3 / DB4 / DC34**PACKAGE MECHANICAL DATA** (in millimeters)
DO 35 Glass

Cooling method by convection and conduction
Marking : type number
Weight : 0.15 g

Polarity : N A
Stud torque : N A

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